

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2001-102359

(43)Date of publication of application : 13.04.2001

(51)Int.Cl.

H01L 21/3065  
H01L 21/76

(21)Application number : 11-275256

(71)Applicant : TOSHIBA CORP

(22)Date of filing : 28.09.1999

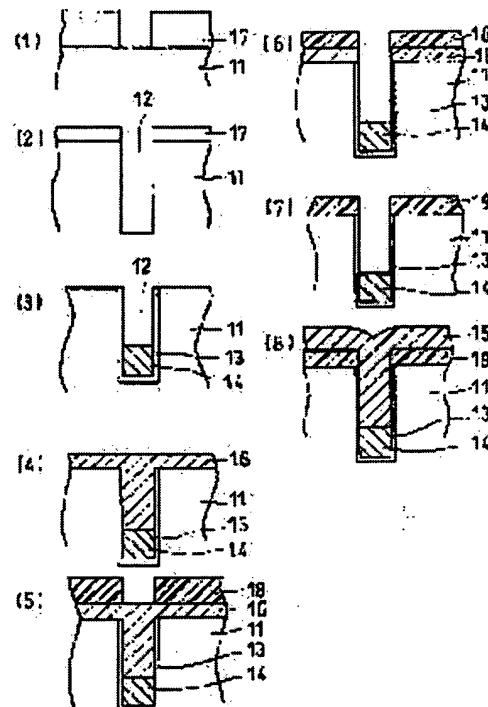
(72)Inventor : SETA SHOJI

## (54) MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

### (57)Abstract:

**PROBLEM TO BE SOLVED:** To obtain a semiconductor device manufacturing method capable of improving a film work in processing accuracy, when the stepped part of the film work is processed by a method where the material or thickness of a mask of an etching stopping layer is selected in a wide range.

**SOLUTION:** This semiconductor device manufacturing method comprises a process, where a processed layer 11 with a stepped part 12 is processed, a mask layer 19 or an etching stopper layer is formed on the stepped part 12 provided to the processed layer 11, and the process is carried out by the use of the mask layer 19 or the stopper layer.



## LEGAL STATUS

[Date of request for examination]

25.08.2004

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

3752405

[Date of registration]

16.12.2005

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]